

Feaures

- EPI wafer
- Low VF and soft recovery characteristic
- Low power loss
- For PFC(DCM/CCM) operation
- Lead free in compliance with EU RoHS 2011/65/EU directive

Mechanical Data

- Circuit figure: Single positive
- Leads: Solderable per mil-std-202, Method 208
- Polarity: as marked
- Mounting torque: 5 in-lbs maximum
- Terminals: Puretin plated
- Weight: 5.15 grams

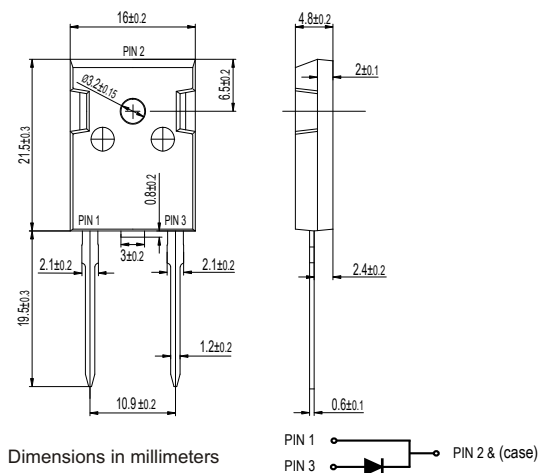
VOLTAGE RANGE

600 Volts

CURRENT

60.0 Amperes

TO-247 AC



MAXIMUM RATINGS(TA=25°C)

RATINGS	SYMBOL	MUR6060	UNIT
Maximum repetitive reverse voltage	VRRM	600	V
Maximum RMS voltage	VRMS	420	V
Maximum DC blocking voltage	VDC	600	V
Maximum average forward current	IAV	60	A
Peak forward surge current,8.3ms single half sine-wave superimposed on rated load	IFSM	560	A
Typical thermal resistance per diode(Note 1)	Rθ-JC	1.5	°C/W
Operating junction temperature range	TJ	-55 to +175	°C
Storage temperature range	TSTG	-55 to +150	°C

Notes: 1. Thermal resistance from junction to case.

MUR6060

ELECTRICAL CHARACTERISTICS (TA=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Instantaneous forward voltage per diode	V _F	I _F = 60A T _J =25°C	-	1.75	2.00	V
		I _F = 60A T _J =125°C	-	-	1.80	V
Reverse current per diode	I _R	V _R =600V T _J =25°C	-	-	50	uA
		V _R =600V T _J =125°C	-	-	500	uA
Reverse recovery time	T _{RR}	I _F = 0.5A I _R =1.0A I _{RR} =0.25A T _J =25°C	-	55	65	ns

RATING AND CHARACTERISTIC CURVES (MUR6060)

FIG. 1 - TYPICAL FORWARD CURRENT DERATING CURVE

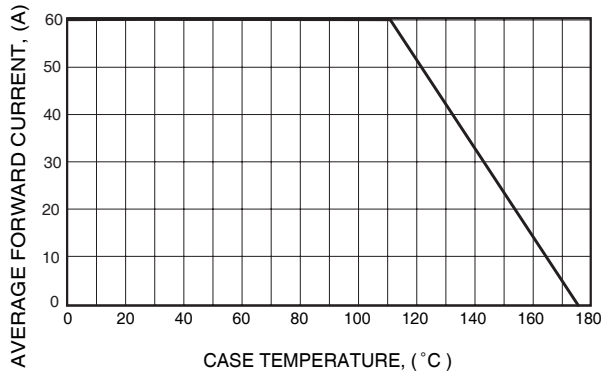


FIG. 2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

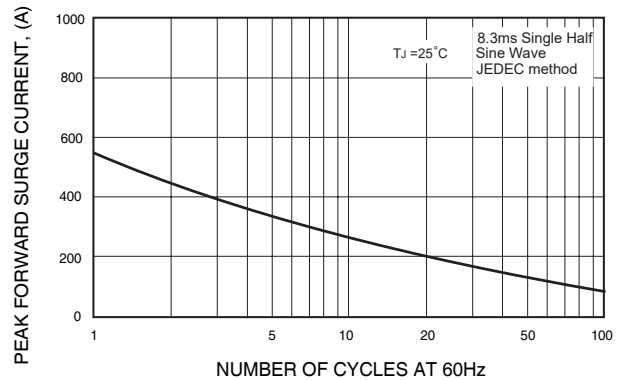


FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

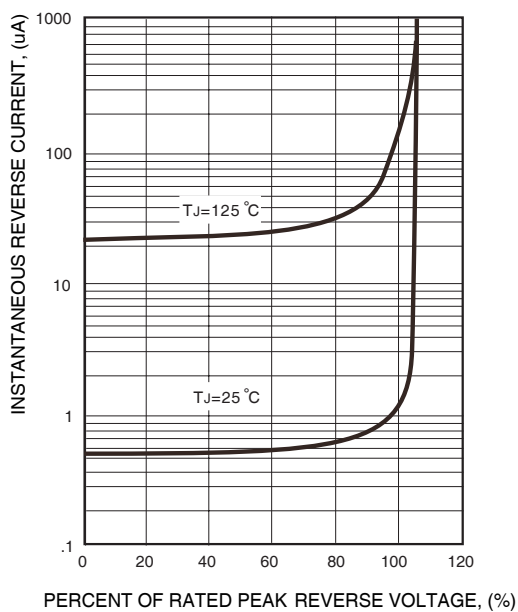


FIG. 4 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

